

### **Amendments to the Claims**

This listing of claims will replace all prior versions, and listings of claims in the application:

#### **Listing of Claims:**

Claims 1-21 (Canceled)

Claim 22 (New): A method for fabricating a semiconductor apparatus, comprising:

fabricating a semiconductor substrate having a first surface in which a semiconductor integrated circuit is formed,

the semiconductor substrate including a conductive layer formed directly on the first surface thereof which is connected to the semiconductor integrated circuit and including a base member of insulating material arranged between the first surface and the conductive layer,

the base member including a first surface facing the first surface of the semiconductor substrate and a second surface opposite the first surface of the base member, and

the conductive layer having an extended portion extending on the second surface of the base member;

providing a connection substrate on which the semiconductor substrate is to be mounted;

placing the semiconductor substrate so that the first surface of the semiconductor substrate faces the connection substrate;

connecting the extended portion of the conductive layer to the connection substrate; and

supplying a seal member in a space between the semiconductor substrate and the connection substrate.

Claim 23 (New): A method according to claim 22, wherein the first surface of the semiconductor substrate is placed to face the connection substrate using a face down technique.

Claim 24 (New): A method according to claim 22, wherein the base member and the seal member are made of a same material having a same thermal expansion coefficient.

Claim 25 (New): A method according to claim 22, wherein the conductive layer and the base member constitute an electrode.

Claim 26 (New): A method according to claim 22, wherein the seal member has a first surface, and has a second surface opposite the first surface of the seal member, the first surface of the seal member being provided on the first surface of the

semiconductor substrate, and the second surface of the seal member being provided as coplanar with an upper surface of the extended portion of the conductive layer.

Claim 27 (New): A method for fabricating a semiconductor apparatus comprising:

forming a semiconductor integrated circuit on a first surface of a semiconductor substrate;

forming a base member of insulating material on the first surface of the semiconductor substrate;

forming a conductive layer directly on the first surface of the semiconductor substrate, the conductive layer being connected to the semiconductor integrated circuit and having an extended portion that extends onto a top surface of the base member;

placing the first surface of the semiconductor substrate having the semiconductor integrated circuit, the base member and the conductive layer thereon as facing a connection substrate;

connecting the extended portion of the conductive layer to the connection substrate; and

supplying a sealing member in a space between the semiconductor substrate and the connection substrate, after said connecting.

Claim 28 (New): A method according to claim 27, wherein the base member and the sealing member are a same material.

Claim 29 (New): A method according to claim 28, wherein the base member and the sealing member have a same thermal expansion coefficient.

Claim 30 (New): A method according to claim 27, wherein the sealing member has a first surface, and has a second surface opposite the first surface of the sealing member,

the first surface of the sealing member being provided on the first surface of the semiconductor substrate, and the second surface of the sealing member being provided as coplanar with an upper surface of the extended portion of the conductive layer.